

*A/cont*

3. (Amended) A [semiconductor] microelectronic workpiece holder [according to] as claimed in claim 1 wherein said contact face plating layer is formed by electroplating said contact face plating material onto the contact face.

4. (Amended) A [semiconductor] microelectronic workpiece holder [according to] as claimed in claim 1 wherein said contact face plating layer is formed from said workpiece plating material.

5. (Amended) A [semiconductor] microelectronic workpiece holder for use in a [semiconductor] microelectronic electroplating apparatus used to plate a metal or metals onto a [semiconductor] microelectronic workpiece, comprising:

a workpiece support mounted to support a [semiconductor] microelectronic workpiece in position with at least a processed surface of the workpiece being in contact with a plating bath;

at least one electrode [finger] which is electrically conductive and capable of receiving and conducting electrical current supplied thereto;

said at least one electrode [finger] having [means forming] a contact face layer forming at least part of said at least one electrode [finger] which is adapted to engage a surface of the [semiconductor] microelectronic workpiece to conduct electrical current [between] therebetween;

wherein said [means forming a] contact face layer is made from a metal-containing contact face material which comprises the same principal metal or metals being [is similar to a workpiece plating material which is to be] plated onto the [semiconductor] microelectronic workpiece.

6. (Amended) A [semiconductor] microelectronic workpiece holder [according to] as claimed in claim 5 wherein said [means forming a] contact face layer is at least 0.1 microns in thickness.

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7. (Amended) A [semiconductor] microelectronic workpiece holder [according to] as claimed in claim 5 wherein said [means forming a] contact face layer is formed by electroplating said contact face material onto the contact face.

8. (Amended) A [semiconductor] microelectronic workpiece holder [according to] as claimed in claim 5 wherein said contact face material is formed from said workpiece plating material.

9. (Amended) A [semiconductor] microelectronic workpiece holder for use in a [semiconductor] microelectronic electroplating apparatus used to plate copper onto a [semiconductor] microelectronic workpiece, comprising:

a workpiece support mounted to support a [semiconductor] microelectronic workpiece in position with at least a processed surface of the workpiece being in contact with a plating bath including a copper-containing workpiece plating material;

at least one electrode [finger] which is electrically conductive and capable of receiving and conducting electrical current supplied thereto;

said at least one electrode [finger] having a contact face forming part thereof which is adapted to engage a surface of the [semiconductor] microelectronic workpiece to conduct electrical current [between] therebetween;

wherein said contact face is pre-conditioned by plating onto said contact face a contact face plating layer made from a copper-containing contact face plating material [which is similar to a copper workpiece plating material which is to be plated onto the semiconductor workpiece].

10. (Amended) A [semiconductor] microelectronic workpiece holder [according to] as claimed in claim 9 wherein said contact face plating layer is at least 0.1 microns in thickness.

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11. (Amended) A [semiconductor] microelectronic workpiece holder [according to] as claimed in claim 9 wherein said contact face plating layer is formed by electroplating said contact face plating material onto the contact face.

12. (Amended) A [semiconductor] microelectronic workpiece holder [according to] as claimed in claim 9 wherein said contact face plating layer is formed from said workpiece plating material.

13. (Amended) A method for plating one or more metals onto the surface of a [semiconductor] microelectronic workpiece, comprising:

contacting a surface of the [semiconductor] microelectronic workpiece with an electrode at a contact face forming a part of the electrode, said contact face being covered by a contact face plating layer, said contact face plating layer being formed from a contact face plating material;

submersing a processed surface of the [semiconductor] microelectronic article into a plating bath which is used to plate a workpiece plating material including one or more metals onto the [semiconductor] microelectronic workpiece;

electroplating workpiece plating material onto the [semiconductor] microelectronic workpiece by passing electrical current between the [semiconductor] microelectronic workpiece and the electrode, said electrical current passing through the contact face plating layer;

wherein the contact face plating material includes the same principal metal or metals being plated onto the microelectronic workpiece.

14. (Amended) A method [according to] as claimed in claim 13 wherein said contact face plating layer is formed from said workpiece plating material.

Please cancel claim 15.

16. (Amended) A method for plating copper onto the surface of a [semiconductor] microelectronic workpiece, comprising:

contacting a surface of the [semiconductor] microelectronic workpiece with an electrode at a contact face forming a part of the electrode, said contact face being covered by a contact face plating layer, said contact face plating layer being formed from a copper-containing contact face plating material;

submersing a processed surface of the [semiconductor] microelectronic article into a plating bath which is used to plate a workpiece plating material including copper onto the [semiconductor] microelectronic workpiece;

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electroplating workpiece plating material onto the [semiconductor] microelectronic workpiece by passing electrical current between the [semiconductor] microelectronic workpiece and the electrode, said electrical current passing through the contact face plating layer.

17. (Amended) A method [according to] as claimed in claim 16 wherein said contact face plating layer is formed from/said workpiece plating material.

Please cancel claim 18.

#### **R E M A R K S**

The present amendment is being filed in response to an Official Action dated March 14, 2000, in which the Examiner rejected pending claims 1-18.

The present application includes a workpiece holder for use in a microelectronic workpiece processing apparatus. More specifically, the workpiece holder is for use in a microelectronic plating apparatus for use in plating a metal or metals onto a microelectronic workpiece. In at least one embodiment, the workpiece holder includes at least one electrode which is electrically conductive which is capable of receiving and conducting electrical current. The electrode includes a contact surface or face which comes into contact with the surface of the microelectronic workpiece. The electrode is capable of conducting electrical current between the surface of the microelectronic workpiece and the electrode.